BAV70 series

High-speed switching diodes Rev. 8 — 18 March 2015

Product data sheet

1. **Product profile**

1.1 General description

High-speed switching diodes, encapsulated in small Surface-Mounted Device (SMD) plastic packages.

Table 1. **Product overview**

Type number	Package			Package	Configuration
	NXP	JEITA	JEDEC	configuration	
BAV70	SOT23	-	TO-236AB	small	dual common cathode
BAV70M	SOT883	SC-101	-	leadless ultra small	dual common cathode
BAV70S	SOT363	SC-88	-	very small	quadruple common cathode/common cathode
BAV70T	SOT416	SC-75	-	ultra small	dual common cathode
BAV70W	SOT323	SC-70	-	very small	dual common cathode

1.2 Features and benefits

- High switching speed: t_{rr} ≤ 4 ns
- Low leakage current
- Small SMD plastic packages
- Low capacitance: C_d ≤ 1.5 pF
- Reverse voltage: V_R ≤ 100 V
- AEC-Q101 qualified

1.3 Applications

- High-speed switching
- General-purpose switching

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
I_R	reverse current	V _R = 80 V	-	-	0.5	μΑ
V_R	reverse voltage		-	-	100	V
t _{rr}	reverse recovery time	[1]	-	-	4	ns

[1] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.



2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Symbol
BAV70; BA	AV70T; BAV70W	'	
1	anode (diode 1)		
2	anode (diode 2)	3	3
3	common cathode	1 2 006aaa144	1 2 006aab034
BAV70M			
1	anode (diode 1)		3
2	anode (diode 2)	1 3	
3	common cathode	2 Transparent top view	1 2 006aab034
BAV70S			
1	anode (diode 1)	По Пт П 4	
2	anode (diode 2)	6 5 4	6 5 4
3	common cathode (diode 3 and diode 4)	0	
4	anode (diode 3)	1 2 3	
5	anode (diode 4)		1 2 3
6	common cathode (diode 1 and diode 2)		006aab104

3. Ordering information

Table 4. Ordering information

Type number	Package					
Name Description		Description	Version			
BAV70	-	plastic surface-mounted package; 3 leads	SOT23			
BAV70M	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883			
BAV70S	SC-88	plastic surface-mounted package; 6 leads	SOT363			
BAV70T	SC-75	plastic surface-mounted package; 3 leads	SOT416			
BAV70W	SC-70	plastic surface-mounted package; 3 leads	SOT323			

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
BAV70	A4*
BAV70M	S4
BAV70S	A4*
BAV70T	A4
BAV70W	A4*

^{[1] * = -:} made in Hong Kong

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode	<u>'</u>				'
V_{RRM}	repetitive peak reverse voltage		-	100	V
V_R	reverse voltage		-	100	V
l _F	forward current				
	BAV70	T _{amb} ≤ 25 °C	-	215	mA
	BAV70M	T _s = 90 °C	-	150	mA
	BAV70S	T _s = 60 °C	-	250	mA
	BAV70T	T _s = 90 °C	-	150	mA
	BAV70W	T _{amb} ≤ 25 °C	-	175	mA
I _{FRM}	repetitive peak forward current				
	BAV70		-	450	mA
	BAV70M		-	500	mA
	BAV70S		-	450	mA
	BAV70T		-	500	mA
	BAV70W		-	500	mA
I _{FSM}	non-repetitive peak forward	square wave [1]			
	current	t _p = 1 μs	-	4	А
		t _p = 1 ms	-	1	А
		t _p = 1 s	-	0.5	Α

^{* =} p: made in Hong Kong

^{* =} t: made in Malaysia

^{* =} W: made in China

 Table 6.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	[2]			
	BAV70	T _{amb} ≤ 25 °C	-	250	mW
	BAV70M	$T_{amb} \le 25 ^{\circ}C$ [3]	-	250	mW
	BAV70S	T _s = 60 °C	-	350	mW
	BAV70T	T _s = 90 °C	-	170	mW
	BAV70W	T _{amb} ≤ 25 °C	-	200	mW
Per device)			'	
I _F	forward current				
	BAV70	T _{amb} ≤ 25 °C	-	125	mA
	BAV70M	T _s = 90 °C	-	75	mA
	BAV70S	T _s = 60 °C	-	100	mA
	BAV70T	T _s = 90 °C	-	75	mA
	BAV70W	T _{amb} ≤ 25 °C	-	100	mA
T _j	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] $T_i = 25$ °C prior to surge.

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode	'					
R _{th(j-a)}	thermal resistance from junction to ambient	in free air [1]				
	BAV70		-	-	500	K/W
	BAV70M	[2]		-	500	K/W
	BAV70W		-	-	625	K/W
R _{th(j-t)}	thermal resistance from junction to tie-point					
	BAV70		-	-	360	K/W
	BAV70W		-	-	300	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point					
	BAV70S		-	-	255	K/W
	BAV70T		-	-	350	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[3] Reflow soldering is the only recommended soldering method.

^[2] Reflow soldering is the only recommended soldering method.

7. Characteristics

Table 8. Characteristics

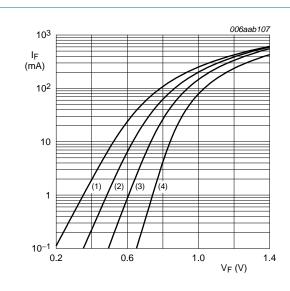
 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode			1			
V_{F}	forward voltage	[1]				
		I _F = 1 mA	-	-	715	mV
		I _F = 10 mA	-	-	855	mV
		I _F = 50 mA	-	-	1	V
		I _F = 150 mA	-	-	1.25	V
I _R	reverse current	V _R = 25 V	-	-	30	nA
		$V_{R} = 80 \text{ V}$	-	-	0.5	μΑ
		V _R = 25 V; T _j = 150 °C	-	-	30	μΑ
		$V_R = 80 \text{ V}; T_j = 150 ^{\circ}\text{C}$	-	-	100	μΑ
C _d	diode capacitance	V _R = 0 V; f = 1 MHz	-	-	1.5	pF
t _{rr}	reverse recovery time	[2]	-	-	4	ns
V_{FR}	forward recovery voltage	[3]	-	-	1.75	V

^[1] Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$

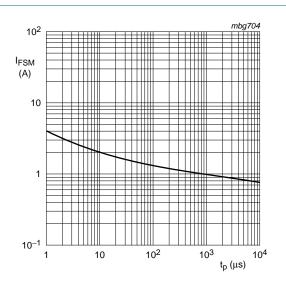
^[2] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 $\Omega;$ measured at I_R = 1 mA.

^[3] When switched from $I_F = 10$ mA; $t_r = 20$ ns.



- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$
- (4) $T_{amb} = -40 \, ^{\circ}C$

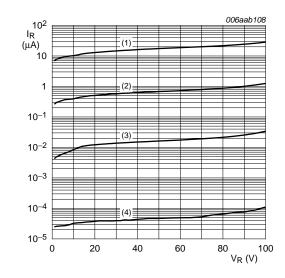
Fig 1. Forward current as a function of forward voltage; typical values



Based on square wave currents.

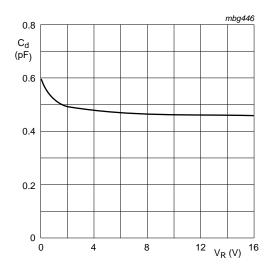
 $T_i = 25$ °C; prior to surge

Fig 2. Non-repetitive peak forward current as a function of pulse duration; maximum values



- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 85 \, ^{\circ}C$
- (3) $T_{amb} = 25 \, ^{\circ}C$
- (4) $T_{amb} = -40 \, ^{\circ}C$

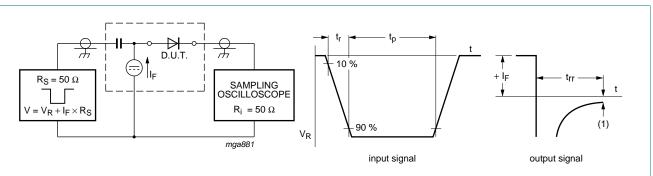
Fig 3. Reverse current as a function of reverse voltage; typical values



f = 1 MHz; T_{amb} = 25 °C

Fig 4. Diode capacitance as a function of reverse voltage; typical values

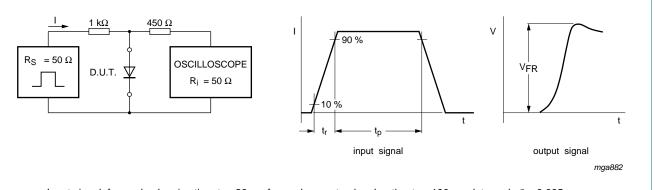
8. Test information



(1) $I_R = 1 \text{ mA}$

Input signal: reverse pulse rise time t_r = 0.6 ns; reverse voltage pulse duration t_p = 100 ns; duty cycle δ = 0.05 Oscilloscope: rise time t_r = 0.35 ns

Fig 5. Reverse recovery time test circuit and waveforms



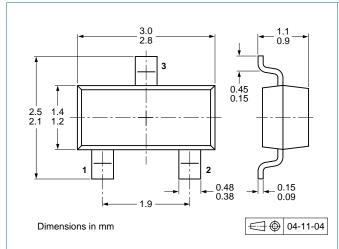
Input signal: forward pulse rise time t_r = 20 ns; forward current pulse duration $t_p \ge 100$ ns; duty cycle $\delta \le 0.005$

Fig 6. Forward recovery voltage test circuit and waveforms

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



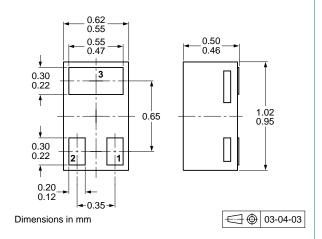
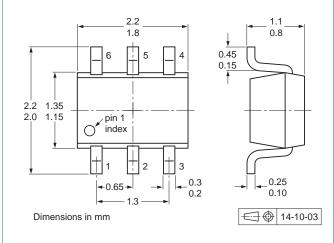


Fig 7. Package outline BAV70 (SOT23/TO-236AB)

Fig 8. Package outline BAV70M (SOT883/SC-101)



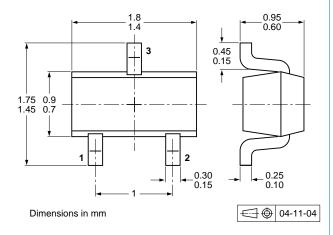


Fig 9. Package outline BAV70S (SOT363/SC-88)

Fig 10. Package outline BAV70T (SOT416/SC-75)

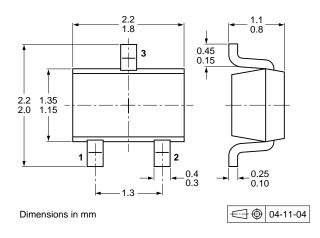


Fig 11. Package outline BAV70W (SOT323/SC-70)

10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

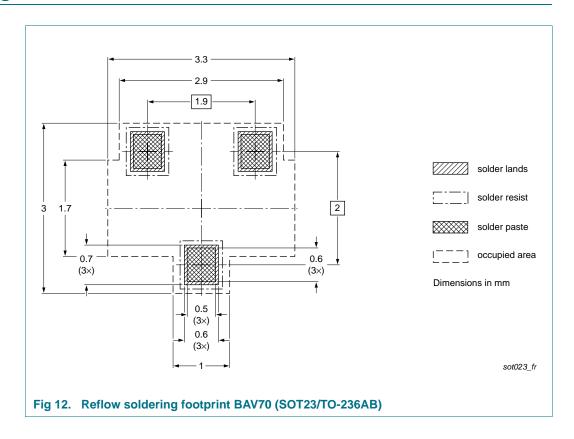
Type number	Type number Package Description		Packing q	uantity
			3000	10000
BAV70	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235
BAV70M	SOT883	2 mm pitch, 8 mm tape and reel	-	-315
BAV70S	SOT363	4 mm pitch, 8 mm tape and reel; T1	-115	-135
		4 mm pitch, 8 mm tape and reel; T2	-125	-165
BAV70T	SOT416	4 mm pitch, 8 mm tape and reel	-115	-135
BAV70W	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135

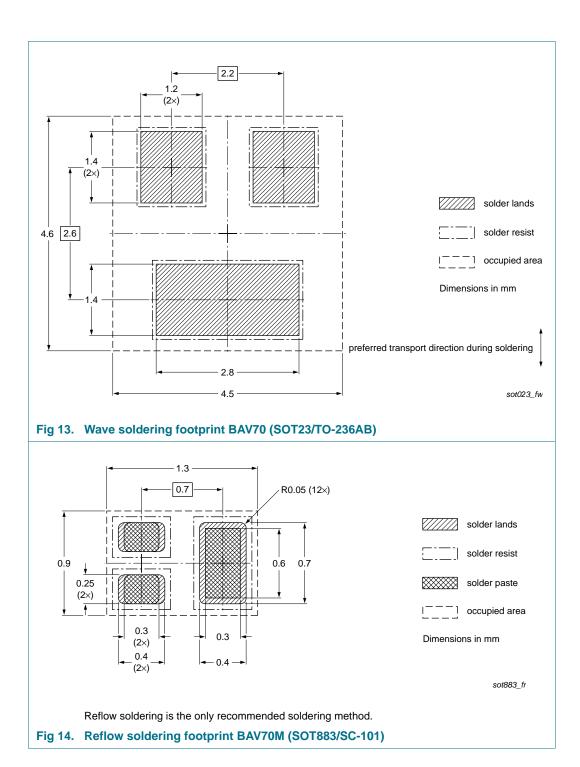
[1] For further information and the availability of packing methods, see Section 14.

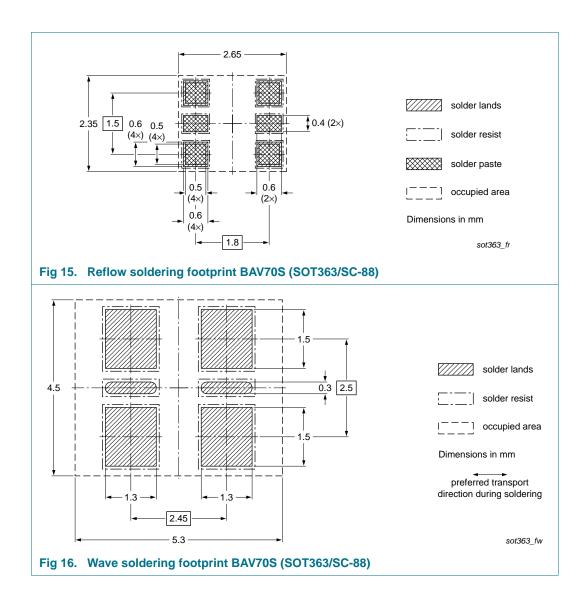
[2] T1: normal taping

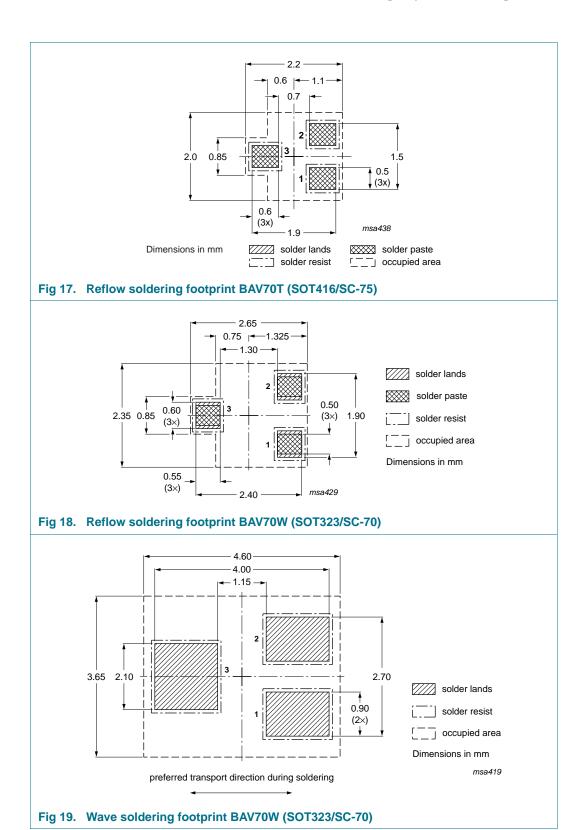
[3] T2: reverse taping

11. Soldering









12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BAV70_SER v.8	20150318	Product data sheet	-	BAV70_SER_7	
Modifications:	 The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 				
 Legal texts have been adapted to the new company name where appropriate. 					
BAV70_SER_7	20071127	Product data sheet	-	BAV70_6 BAV70S_2 BAV70T_3 BAV70W_6	
BAV70_6	20020403	Product specification	-	BAV70_5	
BAV70S_2	19971021	Product specification	-	BAV70S_1	
BAV70T_3	20040204	Product specification	-	BAV70T_2	
BAV70W_6	20020405	Product specification	-	BAV70W_5	

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions"
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BAV70 series

High-speed switching diodes

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